

Title (en)
Semiconductor memory circuit.

Title (de)
Halbleiterspeicherschaltung.

Title (fr)
Circuit de mémoire à semi-conducteur.

Publication
EP 0328458 B1 19940504 (EN)

Application
EP 89400361 A 19890208

Priority
JP 2722088 A 19880208

Abstract (en)
[origin: EP0328458A2] A semiconductor memory circuit comprises a plurality of memory cells (M11 - M22) and a plurality of programming transistors (1), each memory cell being provided at the intersections of one bit line (BL1 - BL3) and one word line (WL1 - WL3). The memory cell includes an insulator (2) and a cell transistor (3), and a conductivity type of the cell transistor selected by a word line select signal is opposite to that of the programming transistor selected by a bit line select signal (Vin). The memory cell is programmed by utilizing an electrical breakdown of the insulator, when the bit line select signal and the word line select signal supplied are in-phase and both the programming transistor and the cell transistor are switched. Therefore, the memory cell is programmed in a short time during which the programming transistor and the cell transistor are switched, and thus this semiconductor memory circuit can be programmed with a low consumption of power and of a high speed.

IPC 1-7
G11C 17/14

IPC 8 full level
G11C 17/14 (2006.01); **G11C 17/04** (2006.01); **G11C 17/16** (2006.01); **H01L 21/8246** (2006.01); **H01L 27/112** (2006.01)

CPC (source: EP KR US)
G11C 11/34 (2013.01 - KR); **G11C 17/00** (2013.01 - KR); **G11C 17/04** (2013.01 - EP US); **G11C 17/08** (2013.01 - KR);
G11C 17/16 (2013.01 - EP US)

Cited by
WO9807161A1

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 0328458 A2 19890816; **EP 0328458 A3 19920102**; **EP 0328458 B1 19940504**; DE 68915018 D1 19940609; DE 68915018 T2 19940818; JP H01204298 A 19890816; KR 890013652 A 19890925; KR 920008246 B1 19920925; US 5079746 A 19920107

DOCDB simple family (application)
EP 89400361 A 19890208; DE 68915018 T 19890208; JP 2722088 A 19880208; KR 890001414 A 19890208; US 30696189 A 19890207